

Subminiature High Sensitivity Photo Interrupter ITR8307

Features:

ITR:

- FAST RESPONSE TIME.
- HIGHLY ANALYTICAL.
- CUTTING WAVELENGTH λp=840nm.
- THIN.
- COMPACT.

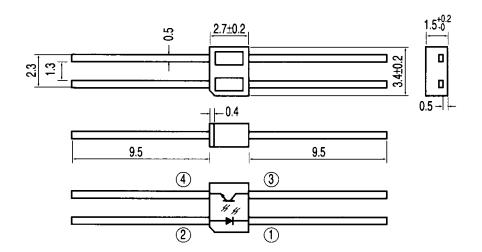
Descriptions:

The ITR8307 reflective sensors consist of an infrared emitting diode and an NPN silicon photo transistor mounted side by side in a black plastic housing. The photo transistor responds to radiation emitted from the diode only when a reflective object or surface is in the field of view of the detector.

Applications:

- · Camera.
- VCR.
- Floppy disk driver.
- Cassette type recorder.
- Various microcomputer control equipment.

Package Dimensions:





Absolute Maximum Ratings: (Ta=25°C)

| | PARAMETER | SYMBOL | RATING | UNIT |
|-----------------------|-----------------------------|------------------------------|---------|---------|
| Input | Power Dissipation | Pd | 75 | mW |
| | Reverse Voltage | Vr | 5 50 | V mA |
| | Forward Current | If | | |
| | Peak Forward Current(*1) | Peak Forward Current(*1) Ifp | | Α |
| Output | Collector Power Dissipation | Pc | 100 | mW |
| | Collector Current | lc | 30 | mA |
| | C-E Breakdown Voltage | B Vceo | 30 | V |
| | E-C Breakdown Voltage | B Veco | 5 | V |
| Operating Temperature | | Topr | -20~+70 | °C |
| Storage Temperature | | Tstg | -30~+80 | °C |
| Soldering | Temperature(*2) | Tsol 260 | | °C |

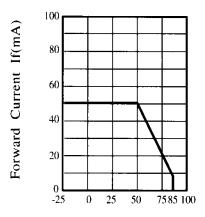
^(*1) Tw=100μsec.,T=10 msec. (*2) 1/16 inch from body for 5 sec

Electro-Optical Characteristics: (Ta=25°C)

| PARAMETER | | SYMBOL | MIN. | TYP. | MAX. | UNIT | CONDITION |
|-----------------|------------------------|--------------|------|------|------|------|--------------------------|
| Input | Forward Voltage | Vf | - | 1.2 | 1.6 | ٧ | If = 20 mA |
| | Reverse Current | lr | - | - | 10 | μA | Vr = 5V |
| | Peak Wavelength | λр | • | 940 | - | nm | - |
| Output | Dark Current | Iceo | - | - | 100 | nA | Vce = 10V |
| | C-E Saturation Voltage | Vce (sat) | - | - | 0.4 | ٧ | Ic = 0.5 mA If = 20mA |
| Light Current | | l. | 0.1 | • | - | mA | Vce = 5V |
| Leakage Current | | Iceod | - | • | 200 | nA | If = 20mA |
| Speed | Rise Time | Tr | - | 25 | - | μSEC | Vcc=2V |
| | Fall Time | Tf | - | 25 | | μSEC | lc=1mA RL=1KΩ |



Fig-1 FORWARD CURRENT VS. AMBIENT TEMPERATURE



Ambient Temperature Ta(°C)

Fig-3 PEAK EMISSION WAVELENGTH VS. AMBIENT TEMPERATURE

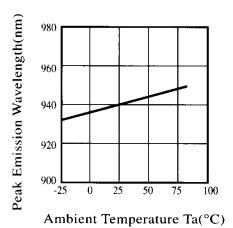


Fig-5 RELATIVE RADIANT FLUX VS. AMBIENT TEMPERATURE

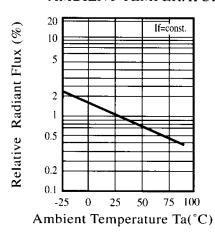
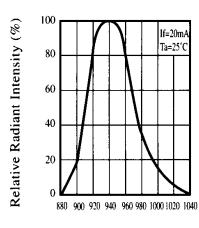


Fig-2 SPECTRAL DISTRIBUTION



Wavelength λ(nm)

Fig-4 FORWARD CURRENT VS. FORWARD VOLTAGE

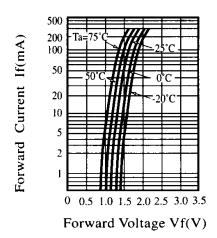


Fig-6 RELATIVE RADIANT INTENSITY VS. ANGULAR DISPLACEMENT

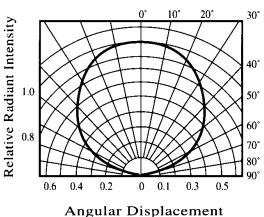




Fig-1 COLLECTOR POWER DISSIPATION VS. AMBIENT TEMPERATURE

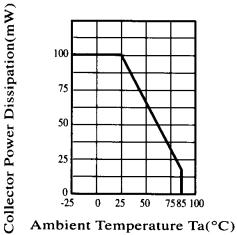


Fig-3 RELATIVE COLLECTOR CURRENT VS. AMBIENT TEMPERATURE

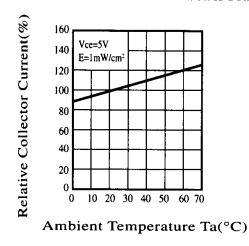


Fig-5 SPECTRAL SENSITIVITY

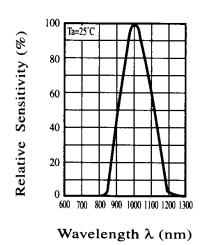


Fig-2 COLLECTOR DARK CURRENT VS. AMBIENT TEMPERATURE

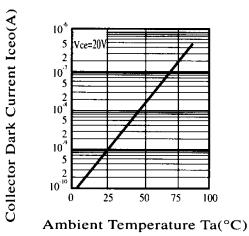


Fig-4 COLLECTOR CURRENT VS. IRRADIANCE

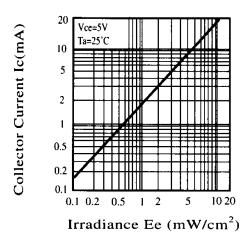
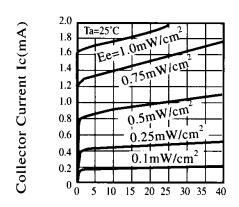


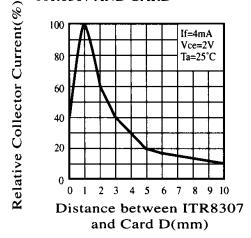
Fig-6 COLLECTOR CURRENT VS. COLLECTOR-EMITTER VOLTAGE



Collector-Emitter Voltage Vce(V)



Fig-1 RELATIVE COLLECTOR CURRENT VS. DISTANCE BETWEEN ITR8307 AND CARD



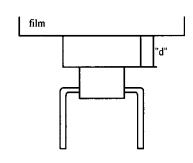
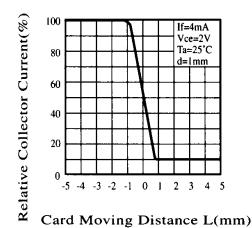
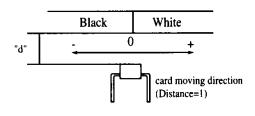


Fig-2 RELATIVE COLLECTOR CURRENT VS. CARD MOVING DISTANCE





RESPONSE TIME VS. LOAD RESISTANCE

